

Description

The AP3428/A is a 1A step-down DC-DC converter. At heavy load, the constant-frequency PWM control performs excellent stability and transient response. No external compensation components are required.

The AP3428/A supports a range of input voltages from 2.5V to 5.5V, allowing the use of a single Li+/Li-polymer cell, multiple Alkaline/NiMH cell, and other standard power sources. The output voltage is adjustable from 0.6V to the input voltage. The AP3428/A employs internal power switch and synchronous rectifier to minimize external part count and realize high efficiency. During shutdown, the input is disconnected from the output and the shutdown current is less than 1 μ A. Other key features include over-temperature and short circuit protection, and under-voltage lockout to prevent deep battery discharge.

The AP3428/A delivers 1A maximum output current while consuming only 40 μ A of no-load quiescent current. Ultra-low R_{DS(ON)} integrated MOSFETs and 100% duty cycle operation make the AP3428/A an ideal choice for high output voltage, high current applications which require a low dropout threshold. Pulse skip mode allows to maintain high efficiency at light-load conditions.

The AP3428/A is available in TSOT25, TSOT25 (Type SM), U-DFN2020-6 (Type J) packages.

Features

- Output Current: Up to 1A
- Output Voltage: 0.6V to VIN
- Input Voltage: 2.5V to 5.5V
- 0.6V Reference Voltage with ±2% Precision
- 40µA (typ) No Load Quiescent Current
- Shutdown Current: <1µA
- 100% Duty Cycle Operation
- 1.5MHz Switching Frequency
- Internal Soft Start
- No External Compensation Required
- Current Limit Protection
- Thermal Shutdown
- TSOT25, TSOT25 (Type SM), U-DFN2020-6 (Type J) Packages
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

Pin Assignments



TSOT25/TSOT25 (Type SM) for AP3428



TSOT25/TSOT25 (Type SM) for AP3428A



U-DFN2020-6 (Type J)

Applications

- Post DC-DC Voltage Regulation
- Set Top Boxes
- Notebook Computer
- PAD

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Typical Applications Circuit



Pin Descriptions

	Pin Number			
TSOT25/ TSOT25 (Type SM) for AP3428	TSOT25/ TSOT25 (Type SM) for AP3428A	U-DFN2020-6 (Type J)	Pin Name	Function
1	3	2	EN	Enable control input. Force this pin voltage above 1.5V enables the chip, and below 0.4V shuts down the device.
2	2	5	GND	Ground pin
3	5	4	LX	The drains of the internal main and synchronous power MOSFET.
4	1	3	VIN	Bias supply. Chip main power supply pin
5	4	6	FB	Feedback voltage to internal error amplifier, the threshold voltage is 0.6V.
—	—	1	NC	NC



AP3428/A

Functional Block Diagram



(A): TSOT25/TSOT25 (Type SM) for AP3428 (B): TSOT25/TSOT25 (Type SM) for AP3428A

(C): U-DFN2020-6 (Type J)



Absolute Maximum Ratings (Note 4)

Symbol	Parameter	Parameter Rating		Unit
Vin	Input Voltage -0.3 to 6			V
VEN	EN Pin Voltage	-0.3 to VIN+0.	3	V
		-0.3 to VIN+0.	3	V
V _{LX}	LX Pin Voltage	-3V to 7V (<40r	าร)	V
V _{FB}	Feedback Pin Voltage	-0.3 to V _{IN} +0.	3	V
PD	Power Dissipation (on PCB, $T_A = +25^{\circ}C$)	TSOT25 TSOT25 (Type SM)	0.4	W
		U-DFN2020-6 (Type J)	1.89	
ΑLθ	Thermal Resistance (Junction to Ambient)	TSOT25 TSOT25 (Type SM)	220	°C/W
- 57 (U-DFN2020-6 (Type J)	53	
θις	Thermal Resistance (Junction to Case, Simulation)	TSOT25 TSOT25 (Type SM)	130	°C/W
		U-DFN2020-6 (Type J)	25	
TJ	Operating Junction Temperature +155			°C
Тѕтс	Storage Temperature	-55 to +150		°C
V _{MM}	ESD (Machine Model)	200		V
Vнвм	ESD (Human Body Model)	2000		V
Vcdм	ESD (Charge Device Mode)	1000		V

Note 4: Stresses greater than those listed under *Absolute Maximum Ratings* can cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to *Absolute Maximum Ratings* for extended periods can affect device reliability.

Recommended Operating Conditions

Symbol	Parameter	Min	Мах	Unit
Vin	Supply Voltage	2.5	5.5	V
TJ	Junction Temperature Range	-40	+125	°C
TA	Operating Ambient Temperature	-40	+85	°C



Electrical Characteristics (@T_A = +25°C, V_{IN} = 5.0V, V_{OUT} = 2.5V, C_{OUT} = 10µF, L = 2.2µH, unless otherwise specified.)

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
V _{IN}	Input Voltage Range	_	2.5		5.5	V
Vout	Output Voltage Range	_	0.6		Vin	V
lq	Quiescent Current	V _{FB} = 0.65V	_	40	_	μA
Isd	Shutdown Current	V _{EN} = 0V	_	0.1	1	μA
V _{FB}	Regulated Feedback Voltage	_	0.588	0.6	0.612	V
I _{FB}	FB Leakage Current	V _{FB} = 1V	—	_	0.2	μA
Ilim	Peak Inductor Current	_	1.3	_		А
fosc	Oscillator Frequency	_	_	1.5		MHz
	Drain-Source On-State	Isw = 100mA High Side	_	250		mΩ
Rds(on)	Resistance	I _{SW} = 100mA Low Side	_	170		mΩ
Rdisch	Output Discharge Switch On Resister	_	_	2.1	_	kΩ
V _{ENH}	EN Threshold High	—	1.5	_	—	V
VENL	EN Threshold Low	_	_	—	0.4	V
IEN	EN Leakage Current	$V_{IN} = V_{EN} = 5V$	-1.0	_	1.0	μA
Vuvlo	Input UVLO Threshold	_	_	2.4	2.7	V
V _{HYS}	UVLO Hysteresis	_	_	0.1	_	V
T _{OTP}	Over Temperature Protection	_	_	+160	_	°C
Тотн	OTP Hysteresis	_	_	+15		°C
tss	Soft-Start Time		_	2	_	ms



Performance Characteristics (@ $T_A = +25^{\circ}C$, $V_{IN} = 5V$, $V_{OUT} = 1.8V$, unless otherwise specified.)



Efficiency vs. Load Current

Feedback Reference Voltage vs. Temperature



PFET Drain-Source On-State Resistance vs. Temperature







NFET Drain-Source On-State Resistance vs. Temperature



Oscillation Frequency vs. Temperature





Performance Characteristics (@T_A = +25°C, V_{IN} = 5V, V_{OUT} = 1.8V, unless otherwise specified.) (continued)



Short Current Protection (IOUT = 1A)



Load Transient (IOUT=0.1A to 1A)





Enable Turn Off Characteristic (Iout = 1A)

SCP Recovery (Iout = 1A)



Load Transient (IOUT=0.5A to 1A)





Application Information

Typical application circuit is shown in the *Typical Applications Circuit* and for the circuit parameters setting please refers to the following descriptions.

Under Voltage Lockout (UVLO) Circuit

When the V_{IN} drops lower than the UVLO detector threshold, the UVLO circuit starts to operate, V_{REF} stops, and high-side switch and low-side switch built-in switch transistors turn "OFF". As a result, V_{OUT} drops according to the C_{OUT} capacitance value and the load. When the V_{IN} is rising higher than UVLO released voltage, the IC will restart the operation.

Short Circuit Protection and Recovery

When the AP3428/A output node is shorted to GND that V_{FB} drops under 0.42V, AP3428/A will enter hiccup mode to protect itself. If short circuit is removed, and V_{FB} rises over 0.42V, the AP3428/A recovers to normal operation again. If the AP3428/A reaches OCP threshold while short circuit, the AP3428/A will enter cycle by cycle current limit mode until the current under OCP threshold.

Over Temperature Protection

The internal thermal temperature protection circuitry is provided to protect the integrated circuit in the event that the maximum junction temperature is exceeded. When the junction temperature exceeds +160°C, it shuts down the internal control circuit and switching power MOSFET. The AP3428/A will restart automatically under the control of soft start circuit when the junction temperature decreases to +145°C.

Setting the Output Voltage

The output voltage can be adjusted from 1 to 5V using an external resistor divider. Table 1 shows a list of resistor selections for common output voltages. Resistor R1 is selected based on a design tradeoff between efficiency and output voltage accuracy. For high values of R1 there is less current consumption in the feedback network. However the tradeoff is output voltage accuracy due to the bias current in the error amplifier. R1 can be determined by the following equation. Meanwhile, the input capacitor should close to IC for preventing unexpected influences.

$$\mathbf{R1} = \mathbf{R2} \cdot \left(\frac{Vout}{0.6} - \mathbf{1}\right)$$



Figure 1. Feedback Divider Network

Out Voltage	R1	R2	C1
1.0V	91kΩ	120kΩ	22pF
1.2V	100kΩ	100kΩ	22pF
1.5V	150kΩ	100kΩ	22pF
1.8V	300kΩ	150kΩ	22pF
2.5V	380kΩ	120kΩ	22pF
2.8V	440kΩ	120kΩ	22pF
3.3V	430kΩ	100kΩ	22pF

Table 1. Resistor Selection for Common Output



Ordering Information



Part Number	Status	Package	Identification Code	Temperature Range	Packing
AP3428AKTTR-G1	NRND	TSOT25	L2J	-40 to +85°C	3000/Tape & Reel
AP3428KTTR-G1	NRND	TSOT25	L2H	-40 to +85°C	3000/Tape & Reel
AP3428DNTR-G1	Active	U-DFN2020-6(Type J)	CQ	-40 to +85°C	3000/Tape & Reel
AP3428AWT-7	Active	TSOT25 (Type SM)	BD	-40 to +85°C	3000/Tape & Reel
AP3428WT-7	Active	TSOT25 (Type SM)	BC	-40 to +85°C	3000/Tape & Reel

Note 5: NRND = Not Recommended for New Design.

Marking Information

TSOT25 (Type SM) for AP3428WT-7 and AP3428AWT-7



Part Number	Package	Identification Code
AP3428WT-7	TSOT25 (Type SM)	BC
AP3428AWT-7	TSOT25 (Type SM)	BD



Marking Information (continued)

(1) TSOT25 for AP3428

(Top View) LC. 01 **c**12

(2) TSOT25 for AP3428A

(Top View) LO 01 3

First Line: Logo and Marking ID

First Line: Logo and Marking ID

(3) U-DFN2020-6 (Type J)



First Line: Logo and Marking ID





Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: TSOT25 (Type SM)



TSC	DT25 (Type SI	N)	
Dim	Min	Max	Тур	
Α	0.70	0.90	1	
A1	0.00	0.10		
A2	0.70	0.80	0.75	
b	0.35	0.50		
С	0.08	0.20		
D	2.82	3.02	2.92	
E	2.65	2.95	2.80	
E1	1.60	1.70	1.65	
е	0	.95 BSC)	
e1	1	.90 BSC)	
L	0.30	0.60	0.40	
L1	0.59 REF			
L2	0	.25 BSC	>	
а	0°	8°		
All D	All Dimensions in mm			



Package Outline Dimensions (continued)

Please see http://www.diodes.com/package-outlines.html for the latest version.

(2) Package Type: TSOT25



	TSOT25					
Dim	Min	Max	Тур			
Α	-	1.00	-			
A1	0.01	0.10	-			
A2	0.84	0.90	-			
b	0.30	0.45	-			
С	0.12	0.20	-			
D	-	-	2.90			
Е	-	-	2.80			
E1	-	-	1.60			
е	(0.95 BS	C			
e1		1.90 BS	C			
L	0.30	0.50	-			
L2	0.25 BSC					
θ	0°	8°	4°			
θ1	4°	12°	-			
All D	Dimens	ions in	mm			

(3) Package Type: U-DFN2020-6 (Type J)



U-DFN2020-6 (Type J)					
Dim	Min	Max	Тур		
Α	0.50	0.60			
A1	0.00	0.05	0.03		
A3	-		0.203		
b	0.20	0.30	0.25		
D	1.95	2.075	2.00		
D2	1.45	1.65	1.55		
E	1.95	2.075	2.00		
E2	0.76	0.96	0.86		
е	0.65 BSC				
L	0.30	0.40	0.35		
All	Dimens	ions in	mm		



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: TSOT25 (Type SM)



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3.199

(2) Package Type: TSOT25



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3.199

(3) Package Type: U-DFN2020-6 (Type J)



Dimensions	Value (in mm)
С	0.650
G	0.120
Х	0.350
X1	1.650
Y	0.550
Y1	0.960
Y2	2.300



Mechanical Data

TSOT25/TSOT25 (Type SM)

- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish Mate Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.014 grams (Approximate)

U-DFN2020-6 (Type J)

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leads, Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.007 grams (Approximate)

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